# mail

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# HMC636ST89 / 636ST89E

v02.0311

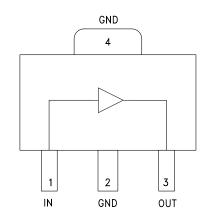


### **Typical Applications**

The HMC636ST89(E) is ideal for:

- Cellular / PCS / 3G
- WiMAX, WiBro, & Fixed Wireless
- CATV & Cable Modem
- Microwave Radio

### **Functional Diagram**



# GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz

#### Features

Low Noise Figure: 2.2 dB High P1dB Output Power: +22 dBm High Output IP3: +40 dBm Gain: 13 dB 50 Ohm I/O's - No External Matching Industry Standard SOT89 Package

### **General Description**

The HMC636ST89(E) is a GaAs pHEMT, High Linearity, Low Noise, Wideband Gain Block Amplifier covering 0.2 to 4.0 GHz. Packaged in an industry standard SOT89, the amplifier can be used as either a cascadable 50 Ohm gain stage, a PA Pre-Driver, a Low Noise Amplifier, or a Gain Block with up to +23 dBm output power. This versatile Gain Block Amplifier is powered from a single +5V supply and requires no external matching components The internally matched topology makes this amplifier compatible with virtually any PCB material or thickness.

### Electrical Specifications, Vs = 5.0 V, $T_A = +25^{\circ} C$

| Parameter                                | Min       | Тур. | Max       | Min. | Тур. | Max. | Units  |
|--|-----------|------|-----------|------|------|------|--------|
| Frequency Range                          | 0.2 - 2.0 |      | 2.0 - 4.0 |      |      | GHz  |        |
| Gain                                     | 10        | 13   |           | 5    | 10   |      | dB     |
| Gain Variation Over Temperature          |           | 0.01 | 0.02      |      | 0.01 | 0.02 | dB/ °C |
| Input Return Loss                        |           | 10   |           |      | 10   |      | dB     |
| Output Return Loss                       |           | 13   |           |      | 15   |      | dB     |
| Reverse Isolation                        |           | 22   |           |      | 20   |      | dB     |
| Output Power for 1 dB Compression (P1dB) | 19        | 22   |           | 20   | 23   |      | dBm    |
| Output Third Order Intercept (IP3)       | 36        | 39   |           | 36   | 39   |      | dBm    |
| Noise Figure                             |           | 2.5  |           |      | 2    |      | dB     |
| Supply Current (Icq)                     |           | 155  |           |      | 155  | 175  | mA     |

Note: Data taken with broadband bias tee on device output.

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# HMC636\* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

# COMPARABLE PARTS

View a parametric search of comparable parts.

### EVALUATION KITS

HMC636ST89 Evaluation Board

### **DOCUMENTATION**

#### **Application Notes**

 AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers

#### Data Sheet

HMC636 Data Sheet

## TOOLS AND SIMULATIONS $\square$

• HMC636 S-Parameter

### REFERENCE MATERIALS

#### **Quality Documentation**

- Package/Assembly Qualification Test Report: 3 Lead Plastic SOT89 Package (QTR: 10002 REV: 02)
- PCN: MS, QS, SOT, SOIC packages Sn/Pb plating vendor change
- Semiconductor Qualification Test Report: PHEMT-F (QTR: 2013-00269)

## DESIGN RESOURCES

- HMC636 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

### DISCUSSIONS

View all HMC636 EngineerZone Discussions.

### SAMPLE AND BUY

Visit the product page to see pricing options.

### TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

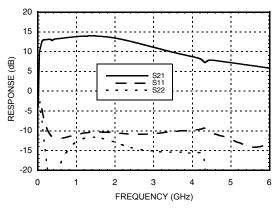
## DOCUMENT FEEDBACK

Submit feedback for this data sheet.

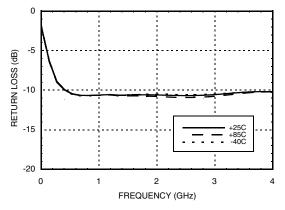




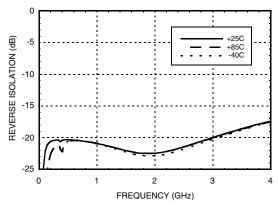
### **Broadband Gain & Return Loss**



Input Return Loss vs. Temperature



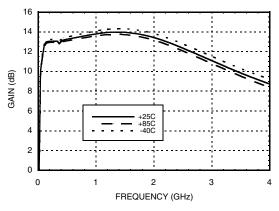
**Reverse Isolation vs. Temperature** 



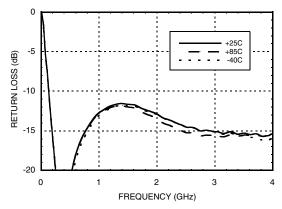
# HMC636ST89 / 636ST89E

# GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz

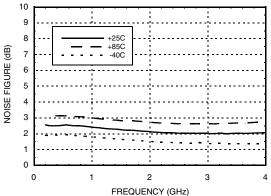
### Gain vs. Temperature



### Output Return Loss vs. Temperature



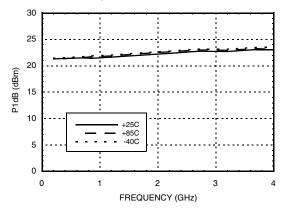
### Noise Figure vs. Temperature



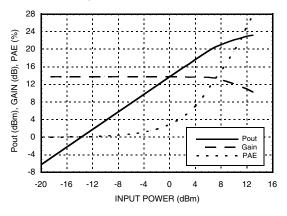




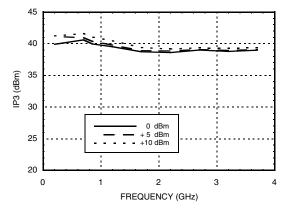
### P1dB vs. Temperature



Power Compression @ 850 MHz

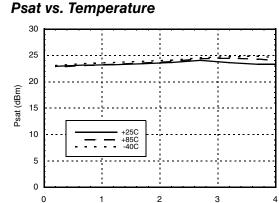


**Output IP3 vs. Input Tone Power** 



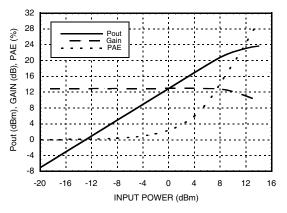
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# GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz

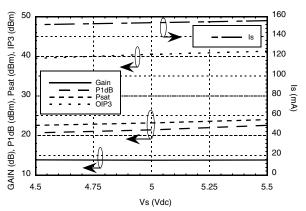




### Power Compression @ 2200 MHz



Gain, Power, Output IP3 & Supply Current vs. Supply Voltage @ 850 MHz



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### Absolute Maximum Ratings

|   | •              |
|---|----------------|
| Collector Bias Voltage (Vcc)                                    | +5.5 Volts     |
| RF Input Power (RFIN)(Vcc = +5 Vdc)                             | +16 dBm        |
| Channel Temperature   | 150 °C         |
| Continuous Pdiss (T = 85 °C)<br>(derate 13.3 mW/°C above 85 °C) | 0.86 W         |
| Thermal Resistance<br>(Channel to lead)                         | 75.6 °C/W      |
| Storage Temperature   | -65 to +150 °C |
| Operating Temperature   | -40 to +85 °C  |
| ESD Sensitivity (HBM)   | Class 1A       |

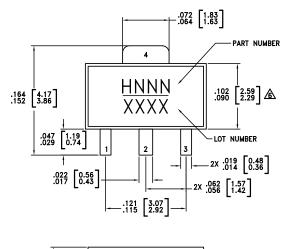


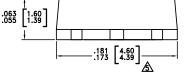
HMC636ST89 / 636ST89E

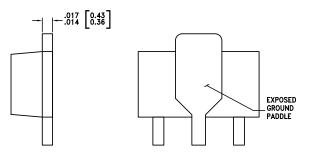
**GaAs PHEMT HIGH LINEARITY** 

Gain Block, 0.2 - 4.0 GHz

### **Outline Drawing**







NOTES:

1. PACKAGE BODY MATERIAL:

MOLDING COMPOUND MP-180S OR EQUIVALENT.

2. LEAD MATERIAL: Cu w/ Ag SPOT PLATING.

3. LEAD PLATING: 100% MATTE TIN.

4. DIMENSIONS ARE IN INCHES [MILLIMETERS]

DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE. 7. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

### Package Information

| Part Number | Package Body Material                              | Lead Finish   | MSL Rating          | Package Marking [3] |
|-------------|--|---------------|---------------------|---------------------|
| HMC636ST89  | Low Stress Injection Molded Plastic                | Sn/Pb Solder  | MSL1 <sup>[1]</sup> | H636<br>XXXX        |
| HMC636ST89E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 <sup>[2]</sup> | <u>H636</u><br>XXXX |

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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# HMC636ST89 / 636ST89E

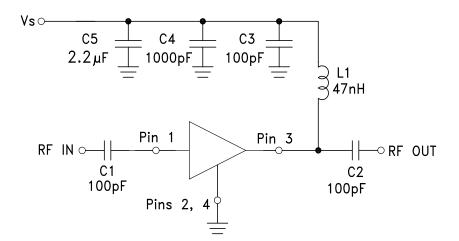
# GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz



### **Pin Descriptions**

| Pin Number | Function | Description  | Interface Schematic |  |
|------------|----------|--|---------------------|--|
| 1          | RFIN     | This pin is DC coupled. An off-chip<br>DC blocking capacitor is required.                    |                     |  |
| 3          | RFOUT    | RF Output and DC BIAS for the amplifier.<br>See Application Circuit for off-chip components. |                     |  |
| 2, 4       | GND      | These pins and package bottom must be connected to RF/DC ground.                             |                     |  |

## **Application Circuit**



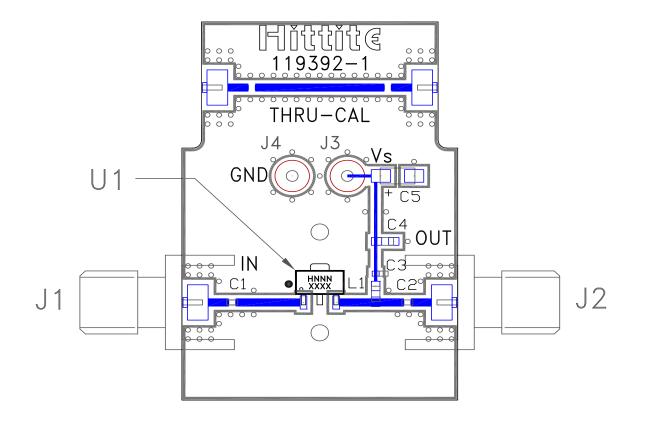


# HMC636ST89 / 636ST89E

# GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz



### **Evaluation PCB**



### List of Materials for Evaluation PCB 119394<sup>[1]</sup>

| Item    | Description                  |  |
|---------|------------------------------|--|
| J1 - J2 | PCB Mount SMA Connector      |  |
| J3 - J4 | DC Pin                       |  |
| C1 - C3 | 100 pF Capacitor, 0402 Pkg.  |  |
| C4      | 1000 pF Capacitor, 0603 Pkg. |  |
| C5      | 2.2 µF Capacitor, Tantalum   |  |
| L1      | 47 nH Inductor, 0603 Pkg.    |  |
| U1      | HMC636ST89(E)                |  |
| PCB [2] | 119392 Evaluation PCB        |  |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: FR4

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

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